

Target specification 5SFG 0980A12000x

1200 V, 980 A*

RoadPak SiC phase-leg module



- $V_{DS} = 1200\text{ V}$
- $I_D = 2 \times 980\text{ A}^*$
- Molded package optimized for EV application
- Pin-fin structure for lowest thermal resistance
- lowest losses thanks to Silicon Carbide chip-set
- main terminals with holes (screw connection) or without holes for welding

*Current rating based on chip rating times number of chips

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	Min.	Max.	Unit
Drain-source voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $T_{vj} \geq 25\text{ °C}$		1200	V
DC drain current	I_D	$T_{Cool} = 55\text{ °C}$, $T_{vj} = 175\text{ °C}$		980	A
Peak drain current	I_{DM}	$t_p = 1\text{ ms}$, duty cycle = 20%, $T_{Cool} = 55\text{ °C}$, $T_{vj} = 175\text{ °C}$		1980	A
Gate-source voltage	V_{GSS}		-4	15	V
Transient gate-source voltage ²⁾	$V_{GSS,max}$	Maximum values under transient events < 50 ns	-8	19	V
DC reverse drain current (body diode)	I_{DR}	$V_{GS} = -4\text{ V}$, $T_{Cool} = 55\text{ °C}$, $T_{vj} = 175\text{ °C}$		350	A
Peak reverse drain current (body diode)	I_{DRM}	$V_{GS} = -4\text{ V}$, $t_p = 1\text{ ms}$		tbd	A
Surge source current (body diode)	I_{SSM}	$V_{GS} = -4\text{ V}$		tbd	A
DC reverse drain current (channel open)	I_{DRS}	$V_{GS} = 15\text{ V}$, $T_{Cool} = 55\text{ °C}$, $T_{vj} = 175\text{ °C}$		980	A
Surge source current (channel open)	I_{SSX}	$V_{GS} = 15\text{ V}$		tbd	A
Isolation voltage	V_{isol}	1 min, $f = 50\text{ Hz}$		4000	V
Junction temperature	T_{vj}			175	°C
Junction operating temperature	$T_{vj(op)}$		-40	175	°C
Storage temperature	T_{stg}		-40	150	°C
Mounting torque	M_s	Module to cooler with M4 screws		2.8	Nm

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

²⁾ Based on chip capability

MOSFET characteristic values ³⁾

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$	$T_{vj} = 175\text{ °C}$	1200		V	
			$T_{vj} = 25\text{ °C}$	1200		V	
			$T_{vj} = -40\text{ °C}$	1200		V	
Static drain-source on-state resistance ⁴⁾	$R_{DS(on)}$	$I_D = 640\text{ A}, V_{GS} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.9	2.1	m Ω
			$T_{vj} = 175\text{ °C}$		3.2	3.4	m Ω
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		2	10	μA
			$T_{vj} = 175\text{ °C}$		6	20	μA
Gate-source leakage current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 15\text{ V}, T_{vj} = 25\text{ °C}$			500	nA	
Gate threshold voltage ²⁾	$V_{GS(th)}$	$I_D = 227\text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25\text{ °C}$	1.7	2.4	3.5	V	
Gate charge ²⁾	Q_G	$I_D = 1000\text{ A}, V_{DS} = 800\text{ V}, V_{GE} = -4\text{ V} \dots +15\text{ V}$		1.84		μC	
Input capacitance ²⁾	C_{ISS}	$V_{DS} = 1000\text{ V}, V_{GS} = 0\text{ V}, T_{vj} = 25\text{ °C}, f = 100\text{ kHz}$		39		nF	
Internal gate resistance ²⁾	R_{Gint}			0.41		Ω	
Turn-on switching energy	E_{on}	$V_{DD} = 800\text{ V}, I_D = 640\text{ A}, R_G = 0.47\ \Omega, C_G = 94\text{ nF}, V_{GS} = -4 / +15\text{ V}, L_\sigma = 10\text{ nH}, \text{inductive load}$	$T_{vj} = 25\text{ °C}$		20		mJ
			$T_{vj} = 175\text{ °C}$		25		mJ
Turn-off switching energy	E_{off}	$V_{DD} = 800\text{ V}, I_D = 640\text{ A}, R_G = 1.5\ \Omega, C_G = 94\text{ nF}, V_{GS} = -4 / +15\text{ V}, L_\sigma = 10\text{ nH}, \text{inductive load}$	$T_{vj} = 25\text{ °C}$		19		mJ
			$T_{vj} = 175\text{ °C}$		17		mJ

²⁾ Based on chip capability

³⁾ Characteristic values according to IEC 60747 – 8

⁴⁾ $R_{DS(on)}$ is given at chip level

Body diode characteristic values ⁵⁾

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Diode forward voltage ^{2) 6)}	V_{SD}	$I_S = 200 \text{ A}$, $V_{GS} = -4 \text{ V}$	$T_{vj} = 25 \text{ °C}$	4.6		V
			$T_{vj} = 175 \text{ °C}$	4.2		V
Reverse recovery current	I_{rr}		$T_{vj} = 25 \text{ °C}$	160		A
			$T_{vj} = 175 \text{ °C}$	350		A
Recovered charge	Q_{rr}	$V_R = 800 \text{ V}$, $I_F = 640 \text{ A}$, $V_{GS} = -4 / +15 \text{ V}$, $R_G = 0.47 \text{ } \Omega$, $di/dt = 20 \text{ kA}/\mu\text{s}$ $L_\sigma = 10 \text{ nH}$ inductive load	$T_{vj} = 25 \text{ °C}$	17		μC
			$T_{vj} = 175 \text{ °C}$	22		μC
Reverse recovery time	t_{rr}		$T_{vj} = 25 \text{ °C}$	30		ns
			$T_{vj} = 175 \text{ °C}$	45		ns
Reverse recovery energy	E_{rec}		$T_{vj} = 25 \text{ °C}$	3		mJ
			$T_{vj} = 175 \text{ °C}$	5		mJ

²⁾ Based on chip capability

⁵⁾ Characteristic values according to IEC 60747 – 2

⁶⁾ Forward voltage is given at chip level

Package properties ⁷⁾

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
thermal resistance junction to fluid	$R_{th(j-f)}$	$T_{in} = 55 \text{ °C}$, Coolant: 50% glycol/ 50% water, per switch, 10 l/min, $dP < 120 \text{ mbar}$ water-glycol		91	99	K/kW
Comparative tracking index	CTI		400			V
Module stray inductance	$L_{\sigma DS}$			5		nH
Resistance, terminal-chip	R_{DD+SS}	$T_C = 25 \text{ °C}$		0.117		m Ω
		$T_C = 150 \text{ °C}$		0.227		m Ω

Mechanical properties ⁷⁾

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dimensions	L	AC terminal to DC terminal		110		mm
	W	Mold width		69		mm
	H	Baseplate cooler surface to middle of PCB/pressfit		17.35		mm
Clearance distance in air	d_a	According to IEC 60664-1	Term. to base:	6.9		mm
			Term. to term:	3.3		mm
Surface creepage distance	d_s	According to IEC 60664-1	Term. to base:	8.5		mm
			Term. to term:	8		mm
Mass	m			300		g

⁷⁾ Package and mechanical properties according to IEC 60747 – 15

Electrical configuration

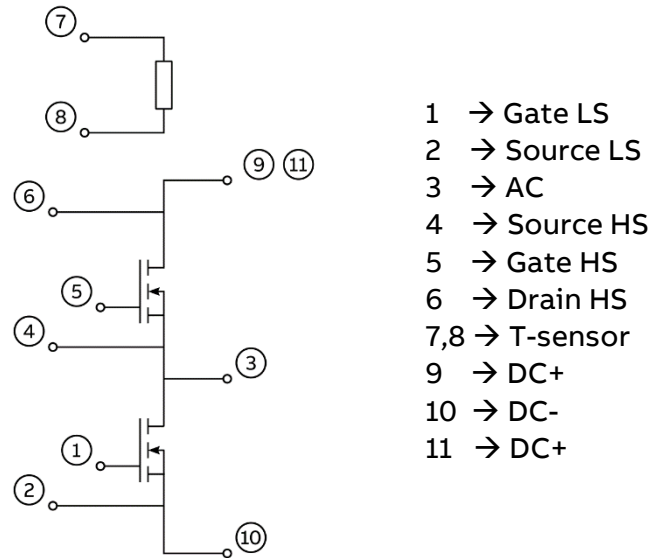


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